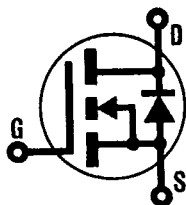


HEXFET® TRANSISTORS**IRF634****IRF635****N-CHANNEL****250 Volt, 0.45 Ohm HEXFET
TO-220AB Plastic Package**

The HEXFET® technology is the key to International Rectifier's advanced line of power MOSFET transistors. The efficient geometry and unique processing of the HEXFET design achieve very low on-state resistance combined with high transconductance and great device ruggedness.

The HEXFET transistors also feature all of the well established advantages of MOSFETs such as voltage control, very fast switching, ease of paralleling, and temperature stability of the electrical parameters.

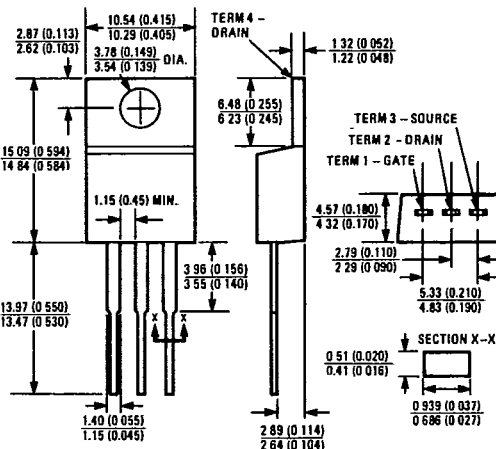
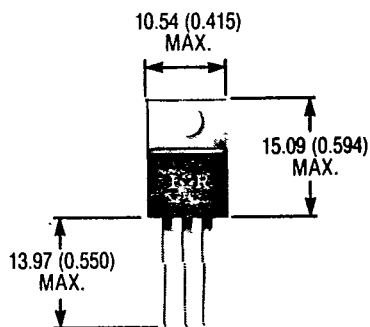
They are well suited for applications such as motor controls, inverters, choppers and audio amplifiers. The voltage rating makes them cost effective for the 115 volt offline switching applications like battery chargers, hand drills, lighting ballasts, washing machines and dryers.

Features

- Compact Plastic Package
- Fast Switching
- Low Drive Current
- Ease of Paralleling
- Excellent Temperature Stability

Product Summary

Part Number	V _{DS}	R _{DS(on)}	I _D
IRF634	250V	0.45	8.1
IRF635	250V	0.68	6.5

CASE STYLE AND DIMENSIONS

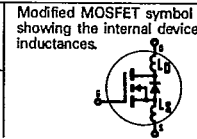
Case Style TO-220AB
Dimensions in Millimeters and (Inches)

Absolute Maximum Ratings

Parameter	IRF634	IRF635	Units
V_{DS} Drain - Source Voltage ①	250	250	V
V_{DGR} Drain - Gate Voltage ($R_{GS} = 20\text{ k}\Omega$) ①	250	250	V
$I_D @ T_C = 25^\circ\text{C}$ Continuous Drain Current	8.1	6.5	A
$I_D @ T_C = 100^\circ\text{C}$ Continuous Drain Current	5.1	4.1	A
I_{DM} Pulsed Drain Current ②	32	26	A
V_{GS} Gate - Source Voltage	± 20		V
$P_D @ T_C = 25^\circ\text{C}$ Max. Power Dissipation	75		W
Linear Derating Factor	0.60		W/K ③
I_{LM} Inductive Current, Clamped	32 (See Fig. 14) $L = 100\text{ }\mu\text{H}$	26	A
I_L Unclamped Inductive Current (Avalanche Current) ③	3.1 (See Fig. 15)		A
T_J Operating Junction and Storage Temperature Range	-55 to 150		$^\circ\text{C}$
Lead Temperature	300 (0.063 in. (1.6mm) from case for 10s)		$^\circ\text{C}$

Electrical Characteristics @ $T_C = 25^\circ\text{C}$ (Unless Otherwise Specified)

Parameter	Type	Min.	Typ.	Max.	Units	Test Conditions
BV_{DSS} Drain - Source Breakdown Voltage	IRF634	250	—	—	V	$V_{GS} = 0\text{V}$
	IRF635	250	—	—	V	$I_D = 250\text{ }\mu\text{A}$
$V_{GS(th)}$ Gate Threshold Voltage	ALL	2.0	—	4.0	V	$V_{DS} = V_{GS}$, $I_D = 250\text{ }\mu\text{A}$
I_{GSS} Gate-Source Leakage Forward	ALL	—	—	500	nA	$V_{GS} = 20\text{V}$
I_{GSS} Gate-Source Leakage Reverse	ALL	—	—	-500	nA	$V_{GS} = -20\text{V}$
I_{DSS} Zero Gate Voltage Drain Current	ALL	—	—	250	μA	$V_{DS} = \text{Max. Rating}$, $V_{GS} = 0\text{V}$
		—	—	1000	μA	$V_{DS} = \text{Max. Rating} \times 0.8$, $V_{GS} = 0\text{V}$, $T_C = 125^\circ\text{C}$
$I_{D(on)}$ On-State Drain Current ④	IRF634	8.1	—	—	A	$V_{DS} > I_{D(on)} \times R_{DS(on)max}$, $V_{GS} = 10\text{V}$
	IRF635	6.5	—	—	A	
$R_{DS(on)}$ Static Drain-Source On-State Resistance ④	IRF634	—	0.40	0.45	Ω	$V_{GS} = 10\text{V}$, $I_D = 4.1\text{A}$
	IRF635	—	0.45	0.68	Ω	
g_{fs} Forward Transconductance ④	ALL	2.9	4.3	—	S(V)	$V_{DS} = 2 \times V_{GS}$, $I_{DS} = 4.1\text{A}$
C_{iss} Input Capacitance	ALL	—	600	—	pF	$V_{GS} = 0\text{V}$, $V_{DS} = 25\text{V}$, $f = 1.0\text{ MHz}$
C_{oss} Output Capacitance	ALL	—	180	—	pF	See Fig. 10
C_{rss} Reverse Transfer Capacitance	ALL	—	52	—	pF	
$t_{d(on)}$ Turn-On Delay Time	ALL	—	9.1	14	ns	$V_{DD} = 125\text{V}$, $I_D \approx 8.1\text{A}$, $R_G = 12\Omega$, $R_D = 15\Omega$
t_r Rise Time	ALL	—	23	35	ns	See Fig. 16
$t_{d(off)}$ Turn-Off Delay Time	ALL	—	31	47	ns	(MOSFET switching times are essentially independent of operating temperature.)
t_f Fall Time	ALL	—	19	29	ns	
Q_g Total Gate Charge (Gate-Source Plus Gate-Drain)	ALL	—	24	35	nC	$V_{GS} = 10\text{V}$, $I_D = 8.1\text{A}$, $V_{DS} = 0.8\text{ Max. Rating}$. See Fig. 17 for test circuit. (Gate charge is essentially independent of operating temperature.)
Q_{gs} Gate-Source Charge	ALL	—	5.1	7.7	nC	
Q_{gd} Gate-Drain ("Miller") Charge	ALL	—	12	18	nC	
L_D Internal Drain Inductance	ALL	—	4.5	—	nH	Measured from the drain lead, 6mm (0.25 in.) from package to center of die.
L_S Internal Source Inductance	ALL	—	7.5	—	nH	Measured from the source lead, 6mm (0.25 in.) from package to source bonding pad.



Thermal Resistance

R_{thJC} Junction-to-Case	ALL	—	—	1.67	K/W ⑤	
R_{thCS} Case-to-Sink	ALL	—	0.50	—	K/W ⑤	Mounting surface flat, smooth, and greased.
R_{thJA} Junction-to-Ambient	ALL	—	—	80	K/W ⑤	Typical socket mount

Source-Drain Diode Ratings and Characteristics

I_S	Continuous Source Current (Body Diode)	IRF634	—	—	8.1	A	Modified MOSFET symbol showing the integral reverse P-N junction rectifier.
		IRF635	—	—	6.5	A	
I_{SM}	Pulse Source Current (Body Diode) ③	IRF634	—	—	32	A	
		IRF635	—	—	26	A	
V_{SD}	Diode Forward Voltage ②	ALL	—	—	2.0	V	$T_C = 25^\circ\text{C}$, $I_S = 8.1\text{A}$, $V_{GS} = 0\text{V}$
t_{rr}	Reverse Recovery Time	ALL	92	190	390	ns	$T_J = 25^\circ\text{C}$, $I_F = 8.1\text{A}$, $dI_F/dt = 100\text{A}/\mu\text{s}$
Q_{RR}	Reverse Recovered Charge	ALL	0.63	1.3	2.7	μC	$T_J = 25^\circ\text{C}$, $I_F = 8.1\text{A}$, $dI_F/dt = 100\text{A}/\mu\text{s}$
t_{on}	Forward Turn-on Time	ALL	Intrinsic turn-on time is negligible. Turn-on speed is substantially controlled by $L_S + L_D$.				

① $T_J = 25^\circ\text{C}$ to 150°C

② Repetitive Rating: Pulse width limited by max. junction temperature. See transient Thermal Response Curve (Fig. 5)

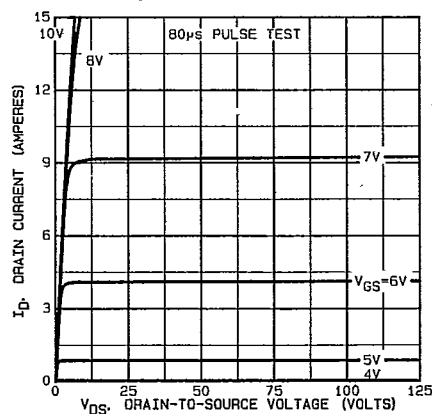
③ $V_{dd} = 25\text{V}$, $T_J = 25^\circ\text{C}$ $L = 100\text{ }\mu\text{H}$ $R_G = 25\Omega$ ④ Pulse Test: Pulse width $\leq 300\text{ }\mu\text{s}$ Duty Cycle $\leq 2\%$ ⑤ $K/W = ^\circ\text{C}/\text{W}$
 $W/K = \text{W}/^\circ\text{C}$ 

Fig. 1 — Typical Output Characteristics

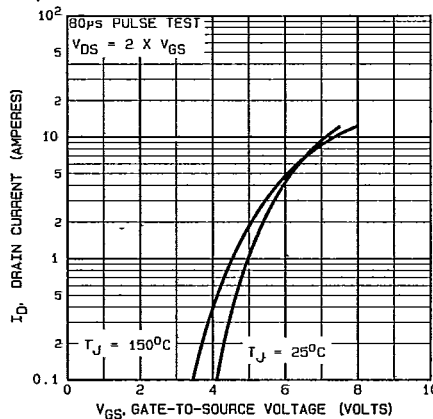


Fig. 2 — Typical Transfer Characteristics

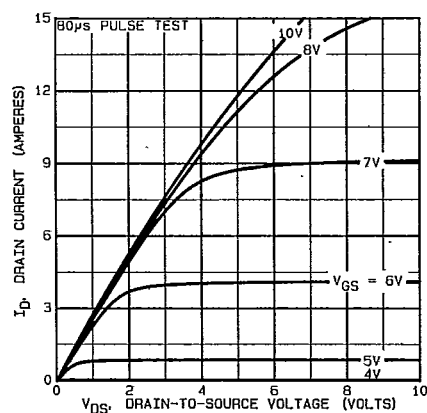


Fig. 3 — Typical Saturation Characteristics

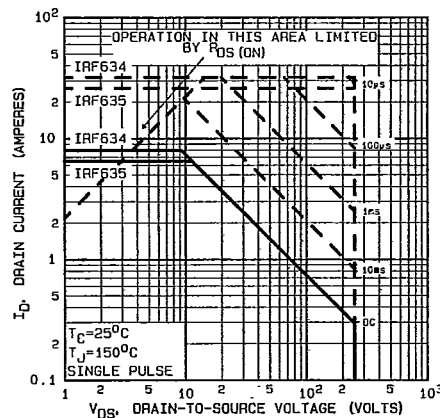


Fig. 4 — Maximum Safe Operating Area

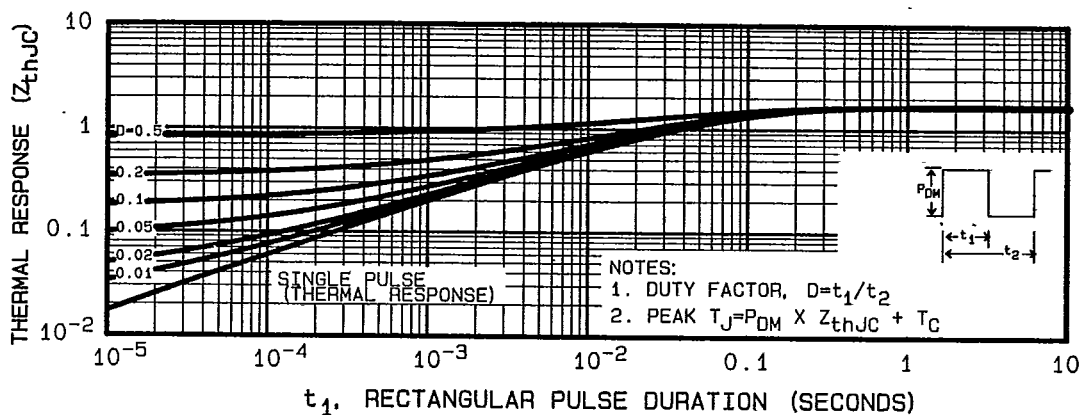


Fig. 5 — Maximum Effective Transient Thermal Impedance, Junction-to-Case Vs. Pulse Duration

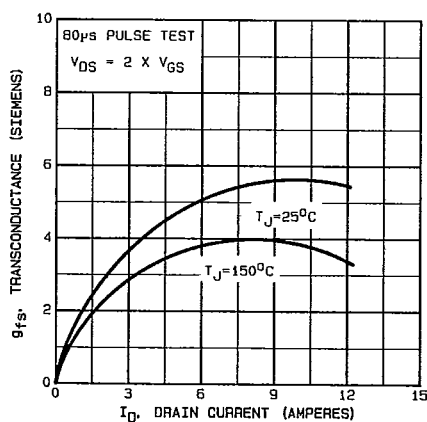


Fig. 6 — Typical Transconductance Vs. Drain Current

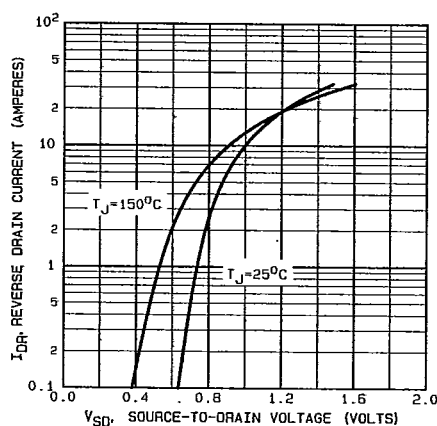


Fig. 7 — Typical Source-Drain Diode Forward Voltage

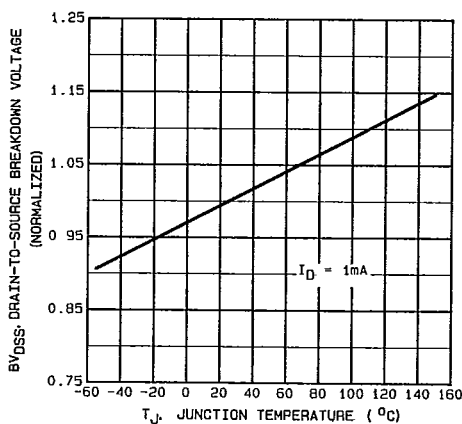


Fig. 8 — Breakdown Voltage Vs. Temperature

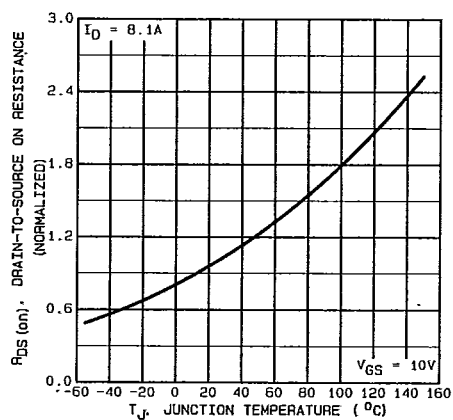


Fig. 9 — Normalized On-Resistance Vs. Temperature

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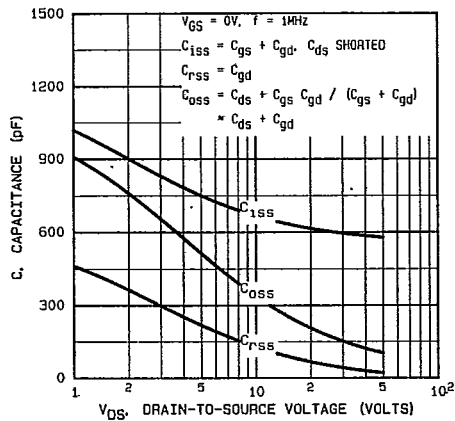


Fig. 10 — Typical Capacitance Vs. Drain-to-Source Voltage

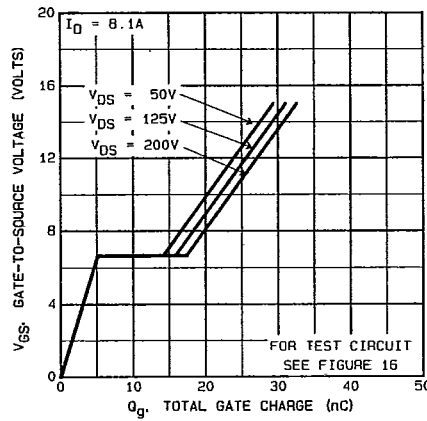


Fig. 11 — Typical Gate Charge Vs. Gate-to-Source Voltage

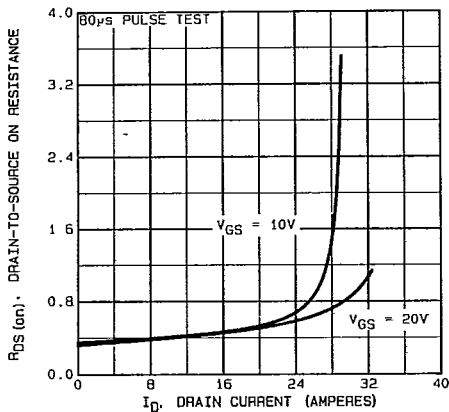


Fig. 12 — Typical On-Resistance Vs. Drain Current

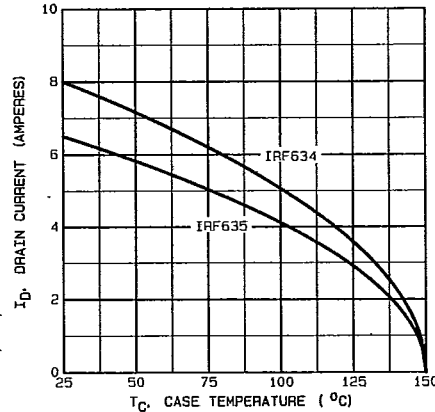


Fig. 13 — Maximum Drain Current Vs. Case Temperature

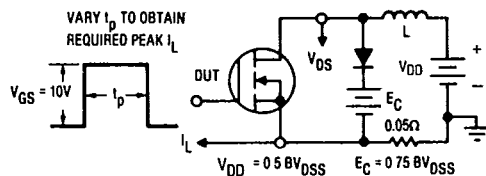


Fig. 14a — Clamped Inductive Test Circuit

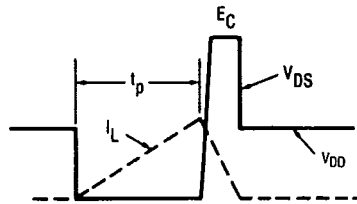


Fig. 14b — Clamped Inductive Waveforms

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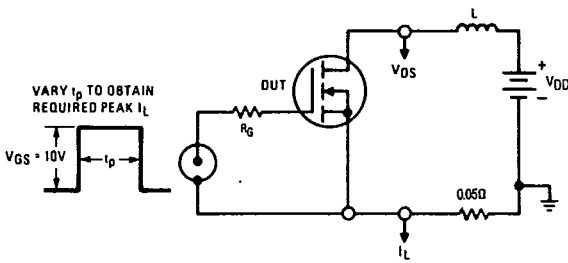


Fig. 15a — Unclamped Inductive Test Circuit

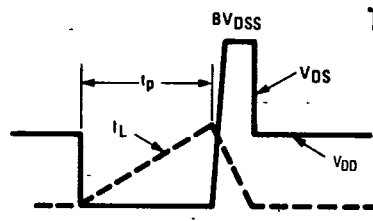


Fig. 15b — Unclamped Inductive Load Test Waveforms

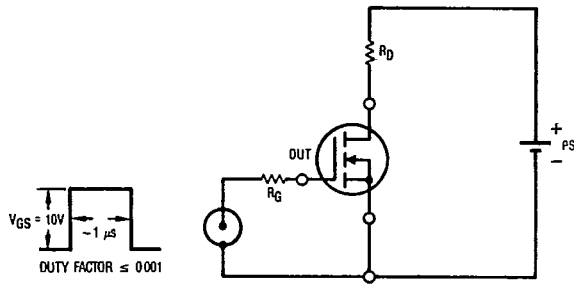


Fig. 16 — Switching Time Test Circuit

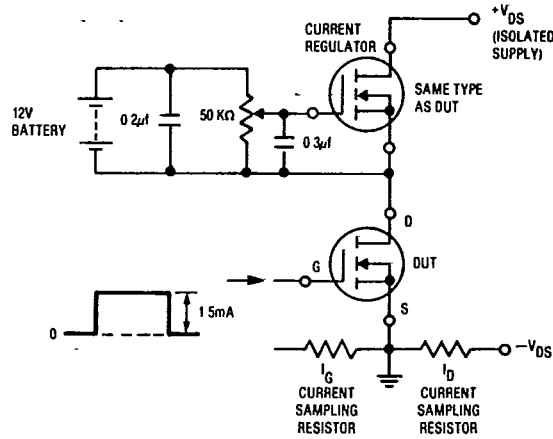
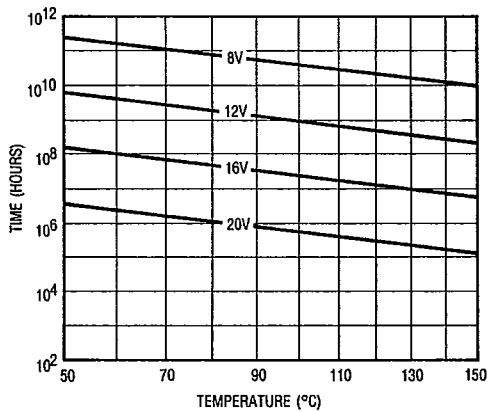
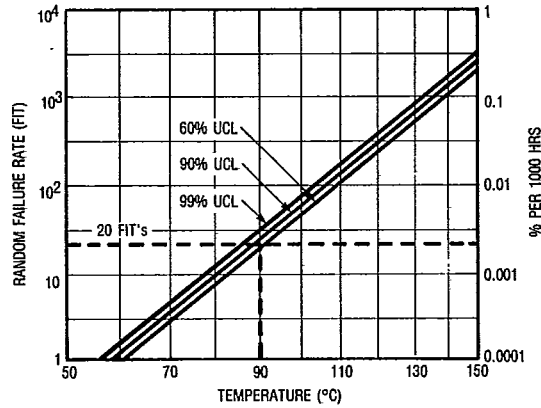


Fig. 17 — Gate Charge Test Circuit



*Fig. 18 — Typical Time to Accumulated 1% Gate Failure



*Fig. 19 — Typical High Temperature Reverse Bias (HTRB) Failure Rate

*The data shown is correct as of April 15, 1987. This information is updated on a quarterly basis; for the latest reliability data, please contact your local IR field office.